

PCN Number:	20231207002.2		PCN Date:	December 21, 2023																			
Title:	Qualification of RFAB as an additional Fab site option, Die Revision, and Assembly BOM options for select devices																						
Customer Contact:	Change Management Team		Dept:	Quality Services																			
Proposed 1st Ship Date:	June 20, 2024		Sample requests accepted until:	Jan 20, 2024*																			
*Sample requests received after Jan 20, 2024 will not be supported.																							
Change Type:																							
<input type="checkbox"/>	Assembly Site	<input checked="" type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Material																		
<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet	<input type="checkbox"/>	Wafer Bump Process																		
<input checked="" type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input checked="" type="checkbox"/>	Wafer Fab Site																		
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site	<input checked="" type="checkbox"/>	Wafer Fab Material																		
<input checked="" type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input checked="" type="checkbox"/>	Wafer Fab Process																		
PCN Details																							
Description of Change:																							
Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab option in addition to BOM options for the devices listed below.																							
<table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th colspan="3">Current Fab Site</th> <th colspan="3">Additional Fab site</th> </tr> <tr> <th>Current Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> <th>Additional Fab site</th> <th>Process</th> <th>Wafer Diameter</th> </tr> </thead> <tbody> <tr> <td>FR-BIP-1</td> <td>ASLC10</td> <td>200mm</td> <td>RFAB</td> <td>LBC7</td> <td>300mm</td> </tr> </tbody> </table>						Current Fab Site			Additional Fab site			Current Fab Site	Process	Wafer Diameter	Additional Fab site	Process	Wafer Diameter	FR-BIP-1	ASLC10	200mm	RFAB	LBC7	300mm
Current Fab Site			Additional Fab site																				
Current Fab Site	Process	Wafer Diameter	Additional Fab site	Process	Wafer Diameter																		
FR-BIP-1	ASLC10	200mm	RFAB	LBC7	300mm																		
The die was also changed as a result of the process change to accommodate the change in Assembly technology																							
Construction differences are as follows:																							
<table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th></th> <th>TI Malaysia</th> <th>TI Malaysia (new)</th> </tr> </thead> <tbody> <tr> <td>Bond wire composition, diameter</td> <td>Cu, 0.96 mil</td> <td>Cu, 0.8 mil</td> </tr> <tr> <td>Wafer thickness</td> <td>267um</td> <td>381um</td> </tr> </tbody> </table>							TI Malaysia	TI Malaysia (new)	Bond wire composition, diameter	Cu, 0.96 mil	Cu, 0.8 mil	Wafer thickness	267um	381um									
	TI Malaysia	TI Malaysia (new)																					
Bond wire composition, diameter	Cu, 0.96 mil	Cu, 0.8 mil																					
Wafer thickness	267um	381um																					
Reason for Change:																							
Supply Continuity																							
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																							
None																							
Impact on Environmental Ratings																							
Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.																							
RoHS		REACH		Green Status																			
<input checked="" type="checkbox"/> No Change		<input checked="" type="checkbox"/> No Change		<input checked="" type="checkbox"/> No Change																			
Changes to product identification resulting from this PCN:																							

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
FR-BIP-1	TID	DEU	Freising
RFAB	RFB	USA	Richardson

Die Rev:**Current****New**

Die Rev [2P]	Die Rev [2P]
A	A

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
TI Malaysia	MLA	MYS	Kuala Lumpur

Sample product shipping label (not actual product label):



(1P) SN74LS07NSR
(Q) 2000 (D) 0336
(31T) LOT: 3959047MLA
(4W) TKY (1T) 7523483SI2
(P)
(2P) REV: (V) 0033317
(20L) CS0: SHE (21L) CC0:USA
(22L) AS0: MLA (23L) AC0: MYS

Product Affected:

TXS0104EQPWRQ1

Qualification Report

Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Approve Date 19-OCTOBER -2023

Product Attributes

Attributes	Qual Device: <u>TXS0104EQPWRQ1</u>	QBS Package, Process Reference: <u>SN74HCS74QPWRQ1</u>
Automotive Grade Level	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125
Product Function	Logic	Logic
Wafer Fab Supplier	RFAB	RFAB
Assembly Site	MLA	MLA
Package Group	TSSOP	TSSOP
Package Designator	PW	PW
Pin Count	14	14

QBS: Qual By Similarity

Qual Device TXS0104EQPWRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TXS0104EQPWRQ1	QBS Package, Process Reference: SN74HCS74QPWRQ1
Test Group A - Accelerated Environment Stress Tests									
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/0/0	3/0/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	1/77/0	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	3/135/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	1/45/0	-
Test Group B - Accelerated Lifetime Simulation Tests									
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	1/77/0	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	3/2400/0
Test Group C - Package Assembly Integrity Tests									
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0
Test Group D - Die Fabrication Reliability Tests									
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDb	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests									
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	3/90/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

Qualification Report

Automotive New Product Qualification Summary (As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

Approve Date 19-OCTOBER -2023

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>TXS0104EQPWRQ1</u>	QBS Reference: <u>SN74HCS74QPWRQ1</u>
Test Group A - Accelerated Environment Stress Tests									
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/0/0	3/0/0
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	3/3/0
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-	3/9/0
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-	3/9/0
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	-	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	-	3/231/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	-	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	-	3/3/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	-	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	-	3/9/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	-	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0

TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0	3/66/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0	3/3/0
TC	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	3/9/0	3/9/0
TC	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	3/9/0	3/9/0
TC	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	3/9/0	3/9/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/231/0	3/231/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	3/3/0
TC	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
TC	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
TC	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	-	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	-	3/135/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	-	3/3/0
Test Group C - Package Assembly Integrity Tests									
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0
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ZVEI ID reference: SEM-PA-08, SEM-DE-03, SEM-PW-13, SEM-PW-02, SEM-PW-09, SEM-PW-03

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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